VS-12TTS08PbF, VS-12TTS08-M3

Vishay Semiconductors

High Voltage Phase Control Thyristor, 12 A



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PRODUCT SUMMARY				
Package	TO-220AB			
Diode variation	Single SCR			
I _{T(AV)}	8 A			
V _{DRM} /V _{RRM}	800 V			
V _{TM}	1.2 V			
I _{GT}	15 mA			
TJ	- 40 °C to 125 °C			

FEATURES

- Designed and qualified according to JEDEC-JESD47
- 125 °C max. operating junction temperature
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS							
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А				

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	UNITS			
I _{T(AV)}	Sinusoidal waveform	8	۸		
I _{T(RMS)}		12.5	A		
V _{DRM} /V _{RRM}		800	V		
I _{TSM}		110	А		
V _T	8 A, T _J = 25 °C	1.2	V		
dV/dt		150	V/µs		
dl/dt		100	A/µs		
TJ	Range	- 40 to 125	°C		

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} AT 125 °C mA				
VS-12TTS08PbF, VS-12TTS08-M3	800	800	1.0				

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}	$T = 109 ^{\circ}\text{C}$ 190° conduction half size ways	8			
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 180° conduction, half sine wave	12.5			
Maximum peak, one-cycle,		10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	95	A		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, $T_J = 125 \ ^{\circ}C$	110			
Maximum 12t fax fusing	l ² t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s		
Maximum I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied, $T_J = 125 \text{ °C}$	64			
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T_J = 125 °C	640	A²√s		
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V		
On-state slope resistance	r _t	T,₁ = 125 °C	16.2	mΩ		
Threshold voltage	V _{T(TO)}	1j = 125 C	0.87	V		
Maximum reverse and direct leakage	1 /1	$T_J = 25 \text{ °C}$	0.05			
current	I _{RM} /I _{DM}	$T_J = 125 \text{ °C}$ $V_R = \text{Rated } V_{RRM}/V_{DRM}$	1.0			
Typical holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ\text{C}$	30	mA		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	50			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 °C, $V_{DRM} = R_g - k = Open$	150	V/µs		
Maximum rate of rise of turned-on current	dl/dt		100	A∕µs		

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}		8.0			
Maximum average gate power	P _{G(AV)}		2.0	W		
Maximum peak positive gate current	+ I _{GM}		1.5	А		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	20	mA		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	15			
ingger		Anode supply = 6 V, resistive load, T_J = 125 °C	10			
		Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	1.2			
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		v		
voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	0.7	v		
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Detectively	0.2	1		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8			
Typical reverse recovery time	t _{rr}	T ₁ = 125 °C	3	μs		
Typical turn-off time	t _q	1j = 125 C	100			

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C	
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5		
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5		
Approvimate weight				2	g	
Approximate weight				0.07	oz.	
Mounting torque	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf ⋅ in)	
Marking device	Case style TO-220AB 12TTS0		rsoa			

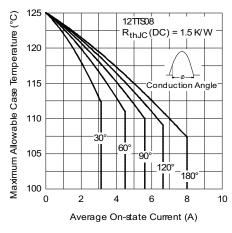


Fig. 1 - Current Ratings Characteristics

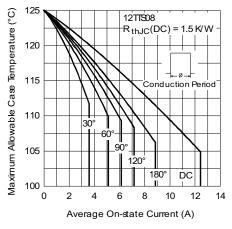


Fig. 2 - Current Ratings Characteristics

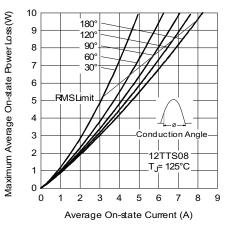


Fig. 3 - On-State Power Loss Characteristics

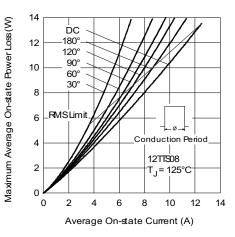


Fig. 4 - On-State Power Loss Characteristics

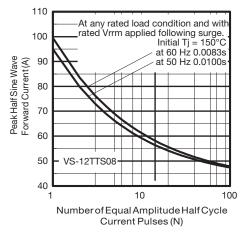
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Fig. 5 - Maximum Non-Repetitive Surge Current

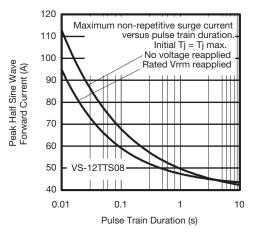


Fig. 6 - Maximum Non-Repetitive Surge Current

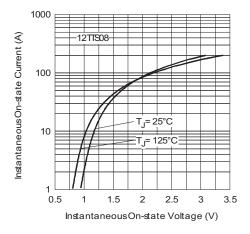


Fig. 7 - On-State Voltage Drop Characteristics

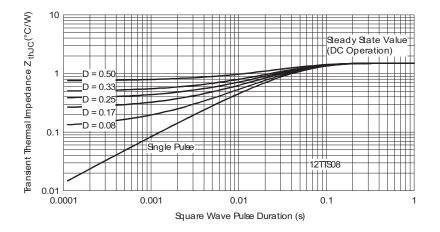


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

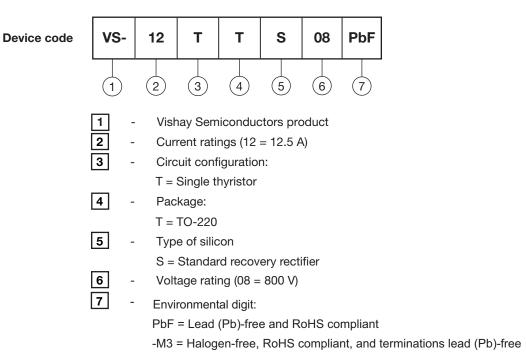
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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-12TTS08PbF	50	1000	Antistatic plastic tubes			
VS-12TTS08-M3	50	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
Dest seculie e information	TO-220AB PbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028				



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TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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